74HC240-Q100; 74HCT240-Q100

Octal buffer/line driver; 3-state; inverting

Rev. 1 — 30 July 2012 Product data sheet

1. General description

The 74HC240-Q100; 74HCT240-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-Power Schottky TTL (LSTTL).

The 74HC240-Q100; 74HCT240-Q100 is a dual octal inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $1\overline{OE}$ and $2\overline{OE}$. A HIGH on $n\overline{OE}$ causes the outputs to assume a high impedance OFF-state.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Inverting 3-state outputs
- Multiple package options
- Complies with JEDEC standard no. 7 A
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC240D-Q100	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HCT240D-Q100				
74HC240PW-Q100	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HCT240PW-Q100				
74HC240BQ-Q100	−40 °C to +125 °C	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1
74HCT240BQ-Q100				

4. Functional diagram

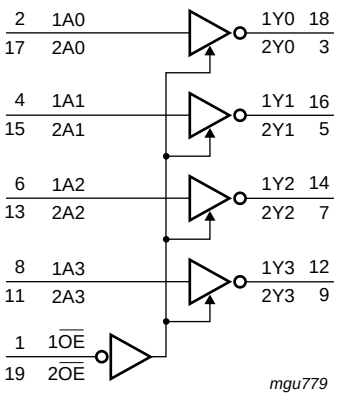


Fig 1. Logic symbol

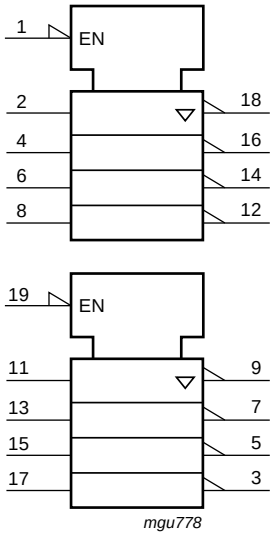


Fig 2. IEC logic symbol

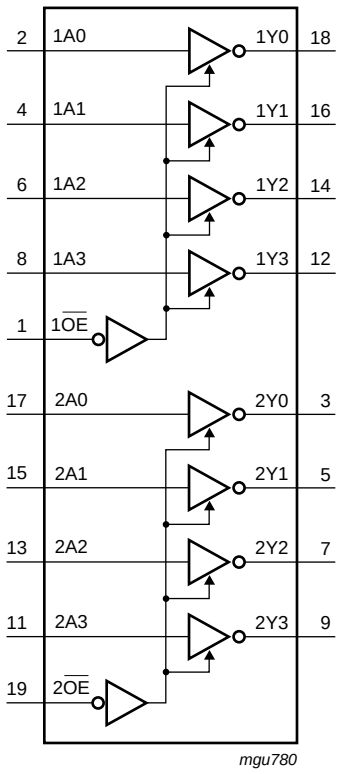


Fig 3. Functional diagram

5. Pinning information

5.1 Pinning

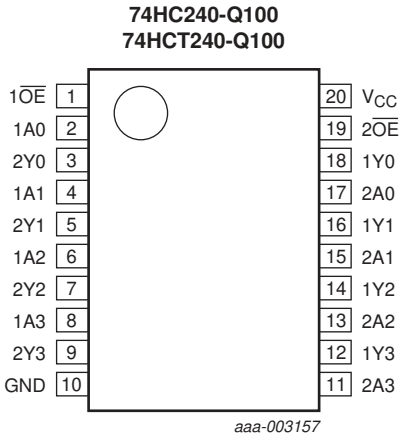
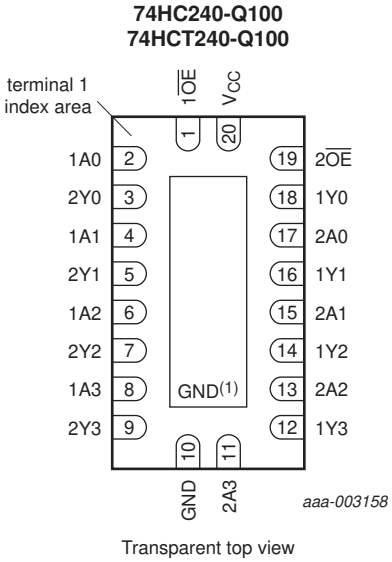


Fig 4. Pin configuration SO20, TSSOP20



Transparent top view

(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 5. Pin configuration DHVQFN20

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$1\overline{OE}$, $2\overline{OE}$	1, 19	output enable input (active LOW)
1A0, 1A1, 1A2, 1A3	2, 4, 6, 8	data input
2Y0, 2Y1, 2Y2, 2Y3	3, 5, 7, 9	bus output
GND	10	ground (0 V)
2A0, 2A1, 2A2, 2A3	17, 15, 13, 11	data input
1Y0, 1Y1, 1Y2, 1Y3	18, 16, 14, 12	bus output
V_{CC}	20	supply voltage

6. Functional description

Table 3. Function table[1]

Input		Output
$\overline{nOE}$	nAn	nYn
L	L	H
L	H	L
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	-0.5 V $< V_O < V_{CC} + 0.5$ V		-	±35	mA
I_{CC}	supply current			-	70	mA
I_{GND}	ground current			−70	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation		[1]	-	500	mW

[1] For SO20 packages: above 70 °C, P_{tot} derates linearly with 8 mW/K.
For TSSOP20 package: above 60 °C, P_{tot} derates linearly with 5.5 mW/K.
For DHVQFN20 packages: above 60 °C, P_{tot} derates linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HC240-Q100						
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	ns/V
		V_{CC} = 4.5 V	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	ns/V
T_{amb}	ambient temperature		−40	-	+125	°C

Table 5. Recommended operating conditions *…continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HCT240-Q100						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 4.5 V	-	1.67	139	ns/V
T_{amb}	ambient temperature		−40	-	+125	°C

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC240-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = −20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = −20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = −20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = −6.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = −7.8 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	per input pin; V_I = V_{IH} or V_{IL}; V_O = V_{CC} or GND; other inputs at V_{CC} or GND; V_{CC} = 6.0 V; I_O = 0 A	-	-	±0.5	-	±5.0	-	±10	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT240-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = –20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 6.0 mA	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	per input pin; V_I = V_{IH} or V_{IL}; V_O = V_{CC} or GND; other inputs at V_{CC} or GND; V_{CC} = 5.5 V; I_O = 0 A	-	-	±0.5	-	±5.0	-	±10	μA
I_{CC}	supply current	V_I = V_{CC} or GND; V_{CC} = 5.5 V; I_O = 0 A	-	-	8.0	-	80	-	160	μA
ΔI_{CC}	additional supply current	per input pin; V_I = V_{CC} – 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; I_O = 0 A								
		nAn or inputs	-	150	540	-	675	-	735	μA
		$n\overline{OE}$ input	-	70	252	-	315	-	343	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; for load circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		Unit
				Min	Typ	Max	Max (85 °C)	Max (125 °C)	
74HC240-Q100									
t_{pd}	propagation delay	nAn to nYn; see Figure 6	[1]						
		V_{CC} = 2.0 V		-	30	100	125	150	ns
		V_{CC} = 4.5 V		-	11	20	25	30	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	9	-	-	-	ns
		V_{CC} = 6.0 V		-	9	17	21	26	ns

Table 7. Dynamic characteristics *…continued*

GND = 0 V; for load circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		Unit
				Min	Typ	Max	Max (85 °C)	Max (125 °C)	
t_{en}	enable time	$n\overline{OE}$ to nYn; see Figure 7	[2]						
		V_{CC} = 2.0 V		-	39	150	190	225	ns
		V_{CC} = 4.5 V		-	14	30	38	45	ns
		V_{CC} = 6.0 V		-	11	26	33	38	ns
t_{dis}	disable time	$n\overline{OE}$ to nYn or see Figure 7	[3]						
		V_{CC} = 2.0 V		-	41	150	190	225	ns
		V_{CC} = 4.5 V		-	15	30	38	45	ns
		V_{CC} = 6.0 V		-	12	26	33	38	ns
t_t	transition time	see Figure 6	[4]						
		V_{CC} = 2.0 V		-	14	60	75	90	ns
		V_{CC} = 4.5 V		-	5	12	15	18	ns
		V_{CC} = 6.0 V		-	4	10	13	15	ns
C_{PD}	power dissipation capacitance	per transceiver; V_I = GND to V_{CC}	[5]	-	30	-	-	-	pF
74HCT240-Q100									
t_{pd}	propagation delay	nAn to nYn; see Figure 6	[1]						
		V_{CC} = 4.5 V		-	11	20	25	30	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	9	-	-	-	ns
t_{en}	enable time	$n\overline{OE}$ to nYn; V_{CC} = 4.5 V; see Figure 7	[2]	-	13	30	38	45	ns
t_{dis}	disable time	$n\overline{OE}$ to nYn; V_{CC} = 4.5 V; see Figure 7	[3]	-	13	25	31	38	ns
t_t	transition time	V_{CC} = 4.5 V; see Figure 6	[4]	-	5	12	15	18	ns
C_{PD}	power dissipation capacitance	per transceiver; V_I = GND to V_{CC} − 1.5 V	[5]	-	30	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

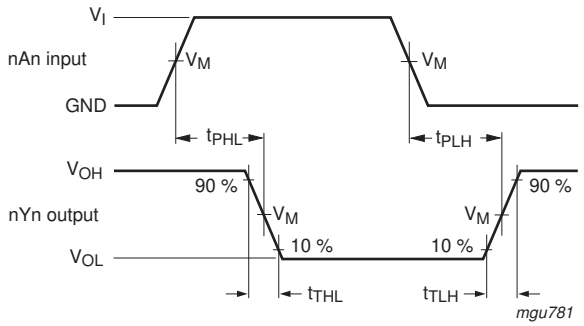
[2] t_{en} is the same as t_{PZH} and t_{PZL}.

[3] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

[4] t_t is the same as t_{THL} and t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

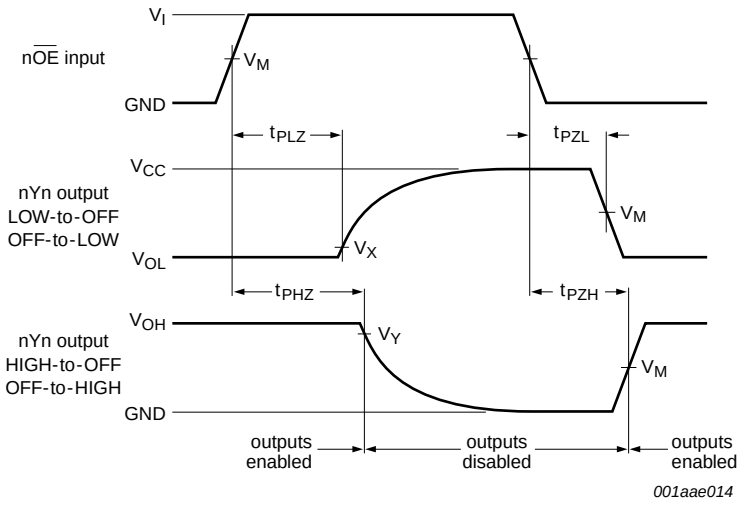
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Input (nAn) to output (nYn) propagation delays and output transition times



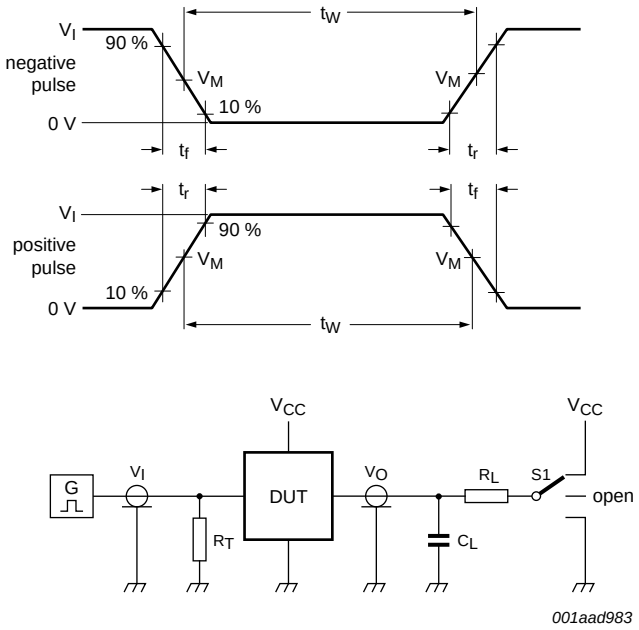
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. 3-state enable and disable times

Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC240-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$
74HCT240-Q100	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$



Test data is given in Table 9.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

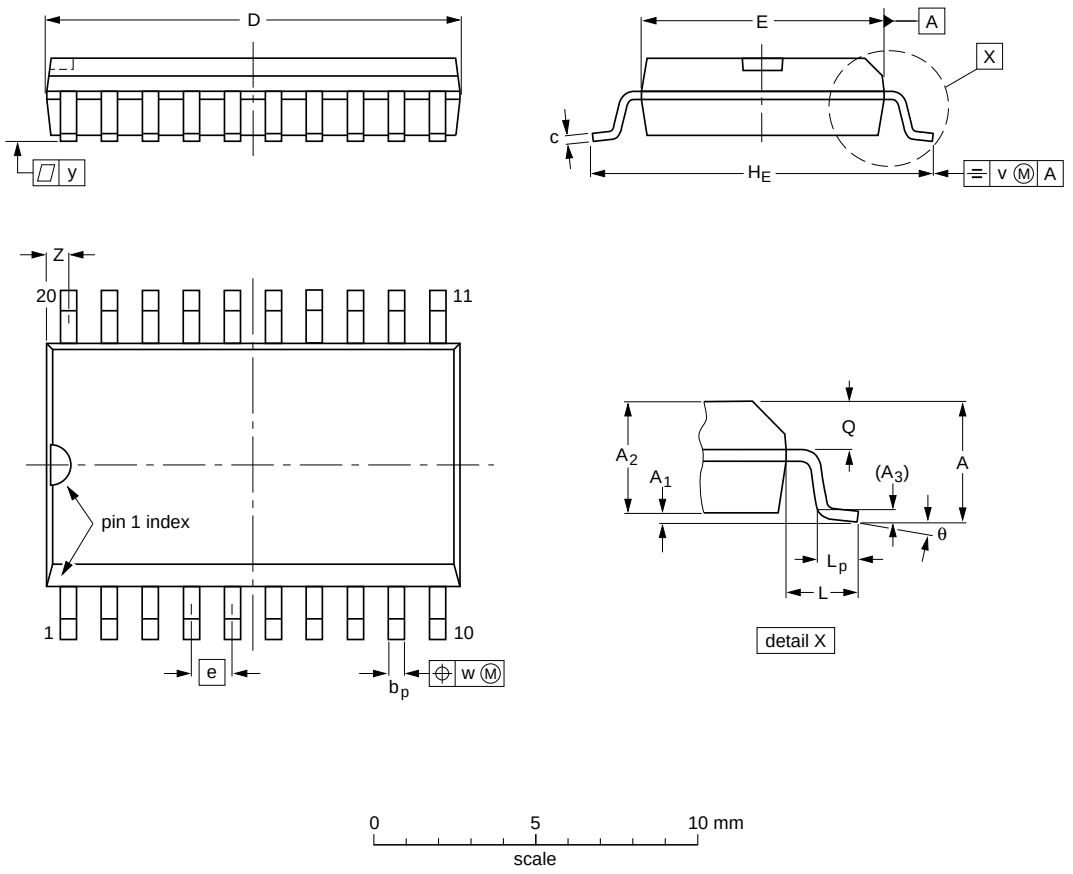
Fig 8. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC240-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74HCT240-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

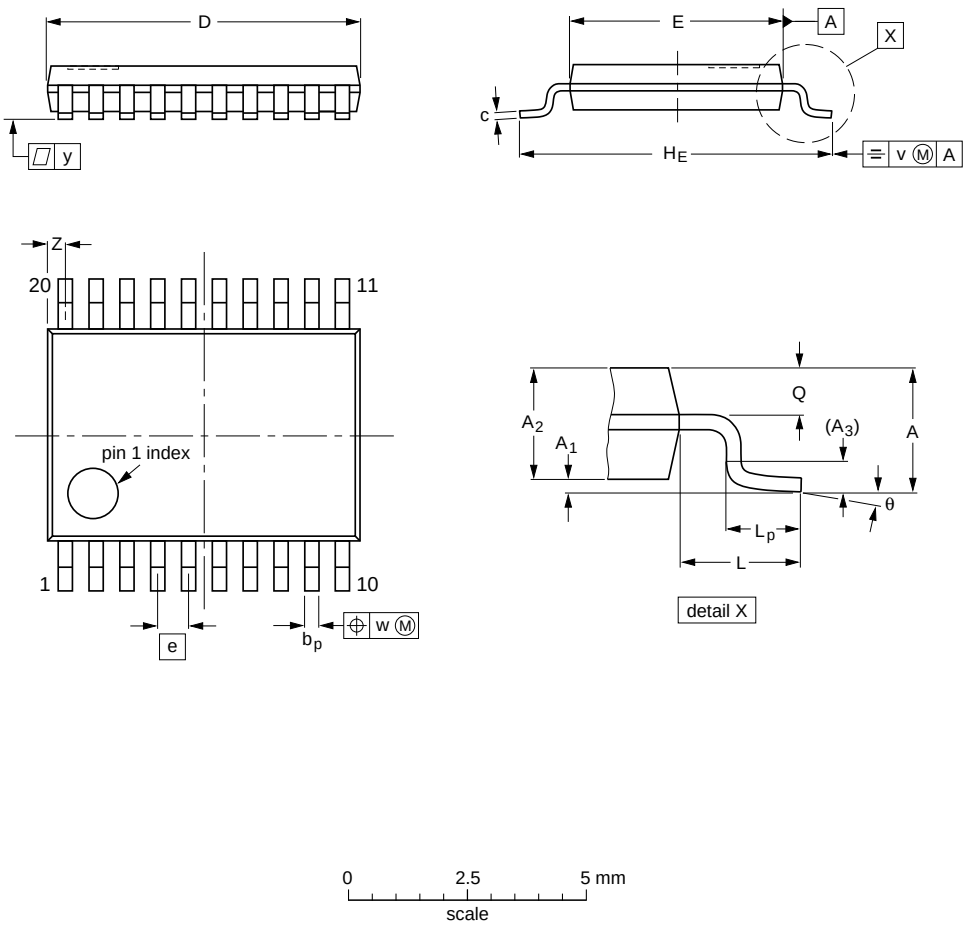
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm **SOT360-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8^o 0^o

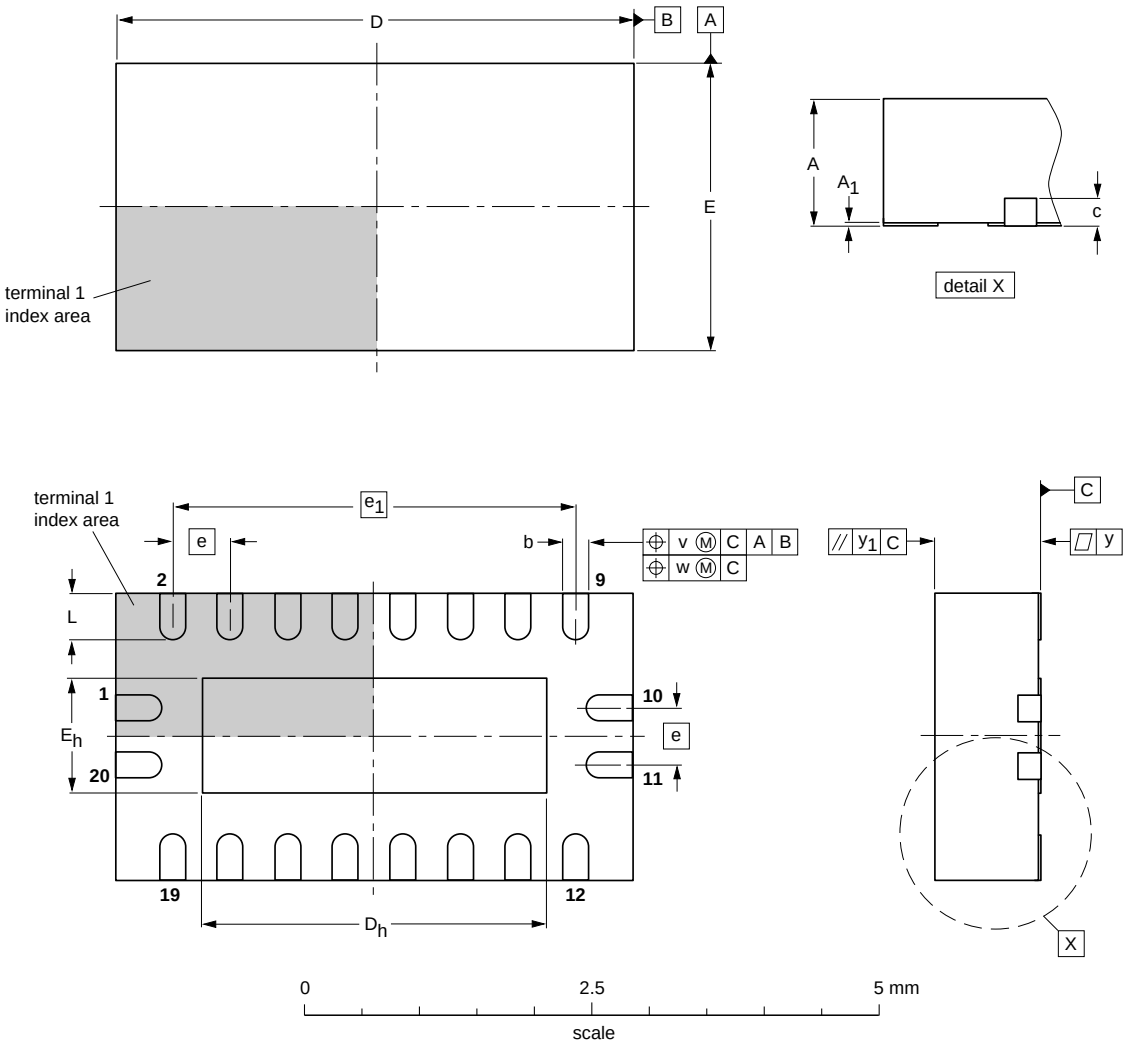
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT360-1		MO-153				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm **SOT764-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	4.6 4.4	3.15 2.85	2.6 2.4	1.15 0.85	0.5	3.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT764-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 11. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT240_Q100 v.1	20120730	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

15.2 Definitions

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16. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

17. Contents

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Date of release: 30 July 2012
Document identifier: 74HC_HCT240_Q100